## DISCRETE SEMICONDUCTORS

## DATA SHEET



# **BAT85**Schottky barrier diode

Product data sheet Supersedes data of 1996 Mar 20 2000 May 25



## Schottky barrier diode

**BAT85** 

#### **FEATURES**

- Low forward voltage
- · Guard ring protected
- Hermetically-sealed leaded glass package.

#### **APPLICATIONS**

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- · Blocking diodes.

#### **DESCRIPTION**

Planar Schottky barrier diode with an integrated protection ring against static discharges, encapsulated in a hermetically-sealed subminiature SOD68 (DO-34) package. The diode is suitable for mounting on a 2 E (5.08 mm) pitch.

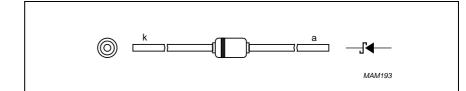


Fig.1 Simplified outline (SOD68; DO-34), pin configuration and symbol.

## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		_	200	mA
I <sub>F(AV)</sub>	average forward current	PCB mounting, lead length = 4 mm; $V_{RWM}$ = 25 V; a = 1.57; $\delta$ = 0.5; $T_{amb}$ = 50 °C; see Fig.2	_	200	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ s}; \delta 0.5$	_	300	mA
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p \le 10 \text{ ms}$	_	5	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

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## **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.3		
		I <sub>F</sub> = 0.1 mA	240	mV
		I <sub>F</sub> = 1 mA	320	mV
		I <sub>F</sub> = 10 mA	400	mV
		I <sub>F</sub> = 30 mA	500	mV
		I <sub>F</sub> = 100 mA	800	mV
$I_R$	reverse current	V <sub>R</sub> = 25 V; see Fig.4	2	μΑ
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.6	4	ns
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; see Fig.5	10	pF

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	320	K/W

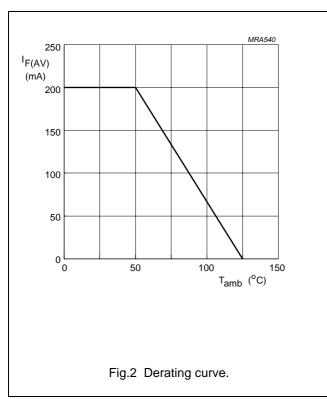
## Note

1. Refer to SOD68 standard mounting conditions.

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## **GRAPHICAL DATA**



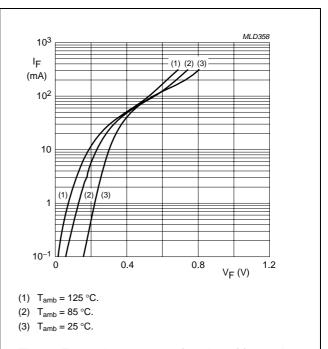


Fig.3 Forward current as a function of forward voltage; typical values.

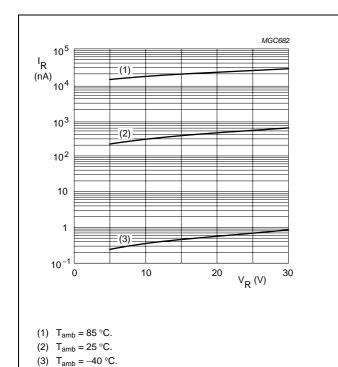
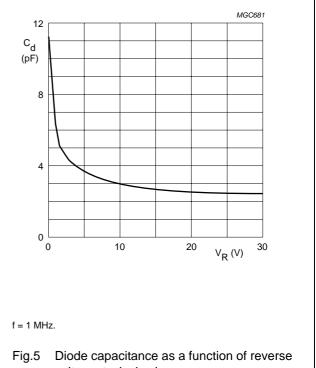


Fig.4 Reverse current as a function of reverse

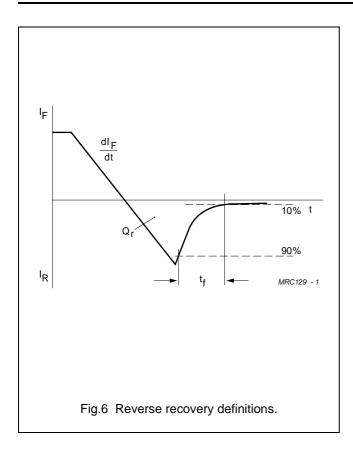
voltage; typical values.



voltage; typical values.

## Schottky barrier diode

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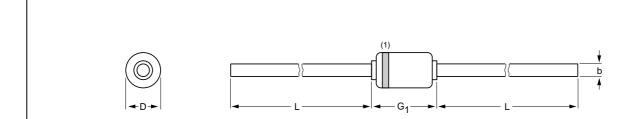
## Schottky barrier diode

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## **PACKAGE OUTLINE**

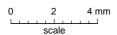
Hermetically sealed glass package; axial leaded; 2 leads

SOD68



## **DIMENSIONS** (mm are the original dimensions)

UNIT	b max.	D max.	G <sub>1</sub> max.	L min.	
mm	0.55	1.6	3.04	25.4	



## Note

1. The marking band indicates the cathode.

OUTLINE		REFERENCES		EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOD68		DO-34				97-06-09

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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2000 May 25

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## **Customer notification**

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